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Attorney's Docket No.: 07977/165002/US3379D1

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APR 02 2002

In the Claims:

Claims 10-21 and 34-39 have been amended as follows. **TECH CENTER 2800**

10. (Amended) [An electronic] A semiconductor device
comprising:

³¹¹
a substrate; [and]

a film [pattern provided] ³¹⁷ comprising aluminum over said
substrate[,]; and (See Fig. 2, see Col. 5, 46⁺ and Cols. 3 and 4)

¹⁹
an insulating film comprising silicon nitride film on said
film;

[wherein said film pattern comprises a part selected from
the group consisting of an electrode and a wiring,

wherein said part of said film pattern comprises aluminum,
and]

wherein said [part of said] film ^{112 (which film?)} [pattern] contains carbon
atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less. (Col. 17, lines 59⁺)

11. (Amended) [A TV camera] A display device ^{Int. use} comprising:

³¹¹
a substrate; [and]

a film pattern provided over said substrate,]

¹⁷
a gate line over said substrate;

¹³
a source line intersected with said gate line over said
substrate; and

¹⁶
a pixel at an intersection of said gate line and said
source line;

[wherein said film pattern comprises a part selected from
the group consisting of an electrode and a wiring,]

wherein said [part of said film pattern] gate line¹⁷
comprises aluminum[,] and

[wherein said part of said film pattern contains] carbon
atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less[;], and

[TV camera parts, coupled to said substrate.]

wherein an insulating film ^{SiN} comprising silicon nitride film
is formed on said gate line.

12. (Amended) A [personal computer] display device^{Int. Use}
comprising:

³¹¹
a substrate; [and

a film pattern provided over said substrate,]

^(613, 66)
a thin film transistor over said substrate, said thin film

transistor having a source region,¹³ a drain region,¹⁷ a channel

³⁰
region between said source and drain region, and a gate

¹²
electrode over said channel region;

¹⁹
an insulating film comprising silicon nitride film on said
gate electrode;

¹⁴
an interlayer insulating film over said thin film
transistor;

(plug connected over 10)

a wiring connected to at least said source region or drain region through a contact hole; and

a pixel¹⁸ electrode over said interlayer insulating film,

[wherein said film pattern comprises a part selected from the group consisting of an] electrode and a wiring,]

wherein [said part of said film pattern] said gate¹⁷ electrode and wiring are formed from a film compris[es]ing aluminum, and

wherein [said part of] said (film)¹¹² [pattern] contains carbon atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less[; and personal computer parts, coupled to said substrate].

13. (Amended) A [car navigation system] semiconductor device comprising:

a substrate; and

a film [pattern provided] comprising aluminum over said substrate,

[wherein said film pattern comprises a part selected from the group consisting of an electrode and a wiring,

wherein said part of said film pattern comprises aluminum, and]

wherein said [part of] said film [pattern] contains carbon atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less[;] and

✓ oxygen atoms at a concentration of 8×10^{18} atoms·cm⁻³ or less

[car navigation parts, coupled to said substrate].

14. (Amended) A [TV projection system] display device
comprising:

a substrate; ³¹¹ [and

a film pattern provided over said substrate,]

a gate line over said substrate;

a source line intersected with said gate line; and

a pixel at an intersection of said gate line and said
source line,

[wherein said film pattern comprises a part selected from
the group consisting of an electrode and a wiring,]

wherein [said part of said film pattern] said gate line
comprises aluminum, [and

[wherein said part of said film pattern contains] carbon
atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less[;] and

oxygen atoms at a concentration of 8×10^{18} atoms·cm⁻³ or less

[TV projection system parts, coupled to said substrate].

15. (Amended) A [video camera] semiconductor device
comprising:

a substrate; [and

a film pattern provided over said substrate,]

a thin film transistor over said substrate, said thin film

transistor having a source region, a drain region, a channel region between said source and drain region, a gate electrode over said channel region;

an interlayer insulating film over said thin film transistor;

a wiring connected to said source or drain region through a contact hole; and

a pixel electrode over said interlayer insulating film,
[wherein said film pattern comprises a part selected from the group consisting of an electrode and a wiring,]

wherein [said part of said film pattern] said gate electrode and wiring are formed from a film compris[es]ing aluminum, and

wherein said [part of said] film [pattern] contains carbon atoms at a concentration of 5×10^{18} atoms·cm⁻³ or less[;] and
[oxygen atoms at a concentration of 8×10^{18} atoms·cm⁻³ or less]

[video camera parts, coupled to said substrate].

✓ 16. (Amended) A semiconductor device according to claim [10] 13, wherein [said substrate comprises glass.] an insulating film comprising silicon nitride film is formed on said film.

✓ 17. (Amended) A [TV camera] display device according to claim [11] 14, wherein [said substrate comprises glass.] an

insulating film comprising silicon nitride film is formed on said gate line.

18. (Amended) A [personal computer] display device according to claim [12] 15, wherein [said substrate comprises glass.] an insulating film comprising silicon nitride film is formed on said gate electrode.

19. (Amended) A [car navigation system] semiconductor device according to claim [13] 40, wherein [said substrate comprises glass.] an insulating film comprising silicon nitride film is formed on said film.

20. (Amended) A [TV projection system] display device according to claim [14] 41, wherein [said substrate comprises glass.] an insulating film comprising silicon nitride film is formed on said gate line.

21. (Amended) A [video camera] display device according to claim [15] 42, wherein [said substrate comprises glass.] an insulating film comprising silicon nitride film is formed on said gate electrode.

112 I 112 34. (Amended) A [An electronic] semiconductor device according to claim 10, wherein said semiconductor device is an [EL] electroluminescence display device [is provided in said electronic device].

112 I 112 35. (Amended) [A TV camera] A semiconductor device according to claim [11] 10, wherein [an EL display] said semiconductor device is [provided in said] a TV camera.

112 I 112 36. (Amended) [A personal computer] A semiconductor device according to claim [12] 10, wherein [an EL display] said semiconductor device is [provided in said] a personal computer.

112 I 112 37. (Amended) [A car navigation system] A semiconductor device according to claim [13] 10, wherein [an EL display] said semiconductor device is [provided in said] a car navigation system.

112 I 112 38. (Amended) [A TV projection system] A semiconductor device according to claim [14] 10, wherein [an EL display device] said semiconductor device is [provided in said] a TV projection system.

I4112 39. (Amended) [A video camera] A semiconductor device
according to claim [11] 10, wherein [an EL display] said
semiconductor device is [provided in said] a video camera.

New claims 40-90 have been added.